NPL PPRIG Proton Therapy Physics Workshop 2016

CMOS Active Pixel Sensors for imaging in proton radiotherapy

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Proton Radiotherapy Verification and Dosimetry Applications

Proton Radiotherapy Verification and Dosimetry Applications

- integrated platform for proton therapy imaging and dosimetry

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ISDI: Image Sensor Design and Innovation Ltd aSpect Systems GmbH Elekta AB (Publ) Advanced Oncotherapy Plc



Royal Society Summer Science Exhibition, July 2014



Proton Radiotherapy Verification and Dosimetry Applications

- integrated platform for proton therapy imaging and dosimetry

More on PRaVDA:

Today at 2:35 pm, N. Allinson "Update: Pravda project imaging update"

Poster session, S. Manger "Development of a phantom for the evaluation of proton CT in proton therapy treatment planning"





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THE PRaVDA INSTRUMENT



WHY CMOS IMAGERS?

Position sensitive detectors

 \circ allow for many protons to be located per R/O cycle, unlike calorimeters or

scintillator stack designs

From moderately radiation tolerant (standard CMOS processes for medical

applications) to radiation hard (HEP experiments)

Large imaging area (12" wafers)

Reticle stitching

Edge-less sensors – 4-side mosaic tiling

• Pixel detectors - x-y hit position

Analog readout – dE/dx measurements





CMOS RT: proton tracking



- CMOS readout speed ~kHz
- Strip readout speed ~MHz
- Need to reconstruct proton tracks in the CMOS RT
- Track following algorithm, based on adaptive velocity calculation and minimisation of layer-to-layer displacement

CMOS RT: proton tracking

Two-layer RT using a 55um pitch CMOS detector And proton tracking based on minimum displacement

(lazi) sun 18 - Fit SNR=3 MA=10 pixel Simulations Exp 0.1 nA Displacement r 10 10 Exp 0.5 nA Gaussian fit (R²=0.998) 10³ Gaussian fit 10 (R²=0.998) Frequency 50 8 10^{-3} 10^{-2} 10^{-1} 10^{0} 10^{1} Occupancy (%) Model Tracking efficiency as a function observed displacement 1.0**Proton track** w/o noise -100 100 -200 0 Displacement (pixel) ↔ ⊷ SNR=2.25 0.8 ------ SNR=3 Tracking efficiency -→ -→ SNR=6 ----- SNR=11 ⊷ ⊷ SNR=21 d ↔ ↔ SNR=101 0.2 Deflection 0.0∟ 6 18 8 14 16 10 12 Displacement M. Esposito 01.12.16 Displacement rms (pixel)

Agreement between simulations and measurements

Fit
w/o noise
Simulated

SNR=3

24

22

CMOS RT: proton tracking

PRaVDA CMOS RT – simulated data: 16 layers, ~1mm Si each + 1mm PMMA

Expected position at layer n+1

 $\begin{cases} \boldsymbol{r}^{exp}(i, n+1) = \boldsymbol{r}^{meas}(i, n) + \hat{\boldsymbol{v}}^{meas}(i, n) \cdot t \\ r_x^{exp}(i, n+1) = d \end{cases}$

Measured position at layer n+1

 $\widetilde{j}: \mathbf{r}^{exp}(i, n+1) - \mathbf{r}^{meas}(\widetilde{j}, n+1) = \min_{1 \le j \le N} [\![\mathbf{r}^{exp}(i, n+1) - \mathbf{r}^{meas}(j, n+1)]\!]^{-0}$

- Need an occupancy of ~0.4% (~90% tracking efficiency)
- With ~10⁹ protons required over 180 projections (100 protons/voxel/projection 1mm³ voxels)
- ~830 Hz CMOS readout for a 5 min pCT scan

Two-layer RT

10⁻¹

Occupancy (%)

100

80

60

40

10⁻²

Fracking efficiency (%)

PRaVDA CMOS RT

10⁰

10

CMOS RT: energy calibration

Range counter



Range distribution (last layer) for mono-energetic protons *(left)*. Calibration curve: mean last layer as function of incident proton energy. Power law fit (Bragg-Kleeman law) is also shown *(right)*.



Energy resolution @60 MeV: 4.4%

M. Esposito 01.12.16

CMOS RT: energy calibration



Range and deposited energy



Total signal in the RT (sum over layers) for mono-energetic protons. Due to the thickness of the CMOS epitaxial layer (18 μ m), spectra are broadened and energy measurements carry large uncertainties (*left*). However, when total energy deposition is analysed for a given last layer, there is a monotonic relation between signal and energy (*right*).

Energy resolution @60 MeV: 2.8%

2 5<u>1e-5</u>

2.0

∧1.5 Ledneuc∧ 1.0

0.5

0.8

CONCLUSIONS

- Several iterations to optimise charge collection in PRaVDA CMOS
- Protons can be tracked through the RT with good efficiency
- kHz readout ensures pCT scan time \leq 5 min
- Increased energy resolution using combining range and energy deposition measurements (2.8% @60 MeV)

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